
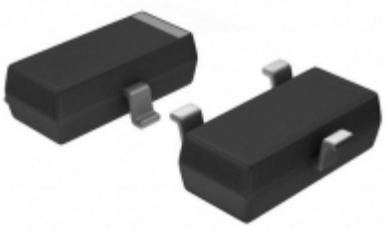
	<h2>SI2369DS-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI2369DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 7.6A TO-236</p> <p>Datenblätter:  SI2369DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 128616 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2369DS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 30V 7.6A TO-236
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	128616 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	TO-236
Verlustleistung (max)	1.25W (Ta), 2.5W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	7.6A (Tc)
Rds On (Max) @ Id, Vgs	29 mOhm @ 5.4A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	36nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1295pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)




SI2369DS-T1-GE3 ist neu im Original, Suche SI2369DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2369DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2369DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2366DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 5.8A SOT-23</p>	 <p>SI2372DS AOS SI2372DS AOS</p>	 <p>SI2372DS-T1-E3 VISHAY SI2372DS-T1-E3 VISHAY</p>	 <p>SI2371EDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 4.8A SOT-23</p>
 <p>SI2369DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 7.6A TO-236</p>	 <p>SI2371EDS-T1-E3 Son SI2371EDS-T1-E3 Son</p>	 <p>SI2371EDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 4.8A SOT-23</p>	 <p>SI2367DS-T1-E3 VISHAY SI2367DS-T1-E3 VISHAY</p>

heiße Teile

Mehr

 SI2343CDS-T1-GE3	 SI2343DS-T1-E3	 SI2343DS-T1-E3	 SI2343DS-T1-GE3	 SI2343DS-T1-GE3
 SI2344DS-E3	 SI2347DS-T1-GE3	 SI2347DS-T1-GE3	 SI2351DS-T1-E3	 SI2351DS-T1-E3
 SI2351DS-T1-GE3	 SI2351DS-T1-GE3	 SI2356DS-T1-GE3	 SI2356DS-T1-GE3	 SI2365EDS
 SI2365EDS-T1-GE3	 SI2365EDS-T1-GE3	 SI2366DS-T1-E3	 SI2366DS-T1-GE	 SI2366DS-T1-GE3
 SI2366DS-T1-GE3	 SI2367DS-T1-E3	 SI2367DS-T1-GE3	 SI2367DS-T1-GE3	 SI2369DS-T1-GE3
 SI2371EDS-T1-GE3	 SI2371EDS-T1-GE3	 SI2372DS-T1-E3	 SI2372DS-T1-GE3	 SI2372DS-T1-GE3
 SI2374DS-T1-GE3	 SI2374DS-T1-GE3	 SI2377DS-T1-GE3	 SI2377EDS	 SI2377EDS-T1-E3
 SI2377EDS-T1-GE3	 SI2377EDS-T1-GE3	 SI2392ADS-T1-E3	 SI2392ADS-T1-GE3	 SI2392ADS-T1-GE3
 SI2392DS-T1-GE3	 SI2392DS-T1-GE3	 SI2399CDS-T1-GE3	 SI2399DS-T1-GE3	 SI2399DS-T1-GE3
 SI2400-B5	 SI2400-F5	 SI2400-FSR	 SI2400-K5	 SI2400-KSR

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